



Freeform Search

Database:	US Pre-Grant Publication Full-Text Database
	US Patents Full-Text Database
	US OCR Full-Text Database
	EPO Abstracts Database
	JPO Abstracts Database
	Derwent World Patents Index
	IBM Technical Disclosure Bulletins

Term:	L2 and (TEMAH or TDEAH or TDMAH)	
		

Display:	<input type="text" value="10"/>	Documents in Display Format:	<input type="text" value="-"/>	Starting with Number	<input type="text" value="1"/>
-----------------	---------------------------------	-------------------------------------	--------------------------------	-----------------------------	--------------------------------

Generate: ☐ Hit List ☒ Hit Count ☐ Side by Side ☐ Image

Search

Clear

Interrupt

Search History

DATE: Friday, February 18, 2005 [Printable Copy](#) [Create Case](#)

Set Name Query
side by side

Hit Count Set Name
result set

DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR

<u>L3</u>	L2 and (TEMAH or TDEAH or TDMAH)	15	<u>L3</u>
<u>L2</u>	L1 and (Hf or hafnium)	2477	<u>L2</u>
<u>L1</u>	(ALD or ALE or (atomic adj layer adj deposition))	76942	<u>L1</u>

END OF SEARCH HISTORY

Refine Search

Search Results -

Terms	Documents
L2 and (ALD or ALE or (atomic adj layer adj deposition))	11

Database:

US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Search:

L3

Refine Search

Recall Text

Clear

Interrupt

Search History

DATE: Friday, February 18, 2005 [Printable Copy](#) [Create Case](#)

Set Name Query

side by side

Hit Count Set Name

result set

DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR

<u>L3</u>	L2 and (ALD or ALE or (atomic adj layer adj deposition))	11	<u>L3</u>
<u>L2</u>	L1 and oxide	969	<u>L2</u>
<u>L1</u>	amino adj functional adj group	1960	<u>L1</u>

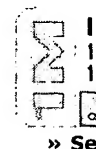
END OF SEARCH HISTORY

IEEE HOME | SEARCH IEEE | SHOP | WEB ACCOUNT | CONTACT IEEE



Membership Publications/Services Standards Conferences Careers/Jobs

IEEE Xplore®
 RELEASE 1.8

 Welcome
 United States Patent and Trademark Office

[Help](#) [FAQ](#) [Terms](#) [IEEE Peer Review](#)
[Quick Links](#)
Welcome to IEEE Xplore®

- ☐ Home
- ☐ What Can I Access?
- ☐ Log-out

Tables of Contents

- ☐ Journals & Magazines
- ☐ Conference Proceedings
- ☐ Standards

Search

- ☐ By Author
- ☐ Basic
- ☐ Advanced
- ☐ CrossRef

Member Services

- ☐ Join IEEE
- ☐ Establish IEEE Web Account
- ☐ Access the IEEE Member Digital Library

IEEE Enterprise

- ☐ Access the IEEE Enterprise File Cabinet

Print Format

 Your search matched **37** of **1128145** documents.

 A maximum of **500** results are displayed, **15** to a page, sorted by **Relevance Descending** order.

Refine This Search:

You may refine your search by editing the current search expression or entering a new one in the text box.

☐ Check to search within this result set

Results Key:
JNL = Journal or Magazine **CNF** = Conference **STD** = Standard

1 Atomic layer deposition of high-/spl kappa/ dielectric for germanium MOS applications - substrate
Chi On Chui; Kim, H.; McIntyre, P.C.; Saraswat, K.C.;

Electron Device Letters, IEEE , Volume: 25 , Issue: 5 , May 2004

Pages:274 - 276

[\[Abstract\]](#) [\[PDF Full-Text \(168 KB\)\]](#) **IEEE JNL**
2 Charge trapping in ultrathin hafnium oxide
Zhu, W.J.; Ma, T.P.; Zafar, S.; Tamagawa, T.;

Electron Device Letters, IEEE , Volume: 23 , Issue: 10 , Oct. 2002

Pages:597 - 599

[\[Abstract\]](#) [\[PDF Full-Text \(201 KB\)\]](#) **IEEE JNL**
3 Atomic layer deposition of high-k thin films for gate and capacitor dielectrics
Senzaki, Y.; Chatham, H.; Park, S.; Bartholomew, L.; Lo, T.; Okuyama, Y.; Ba C.; Tousseau, C.; Fleming, T.; Ford, B.;

Integrated Circuit Design and Technology, 2004. ICICDT '04. International Conference on , 2004

Pages:269 - 274

[\[Abstract\]](#) [\[PDF Full-Text \(582 KB\)\]](#) **IEEE CNF**
4 Influence of metal gate materials and processing on planar CMOS device characteristics with high-k gate dielectrics
Majhi, P.; Young, C.; Bersuker, G.; Wen, H.C.; Brown, G.A.; Foran, B.; Choi, I. Zeitsoff, P.M.; Huff, H.R.;

Solid-State Device Research conference, 2004. ESSDERC 2004. Proceeding of